

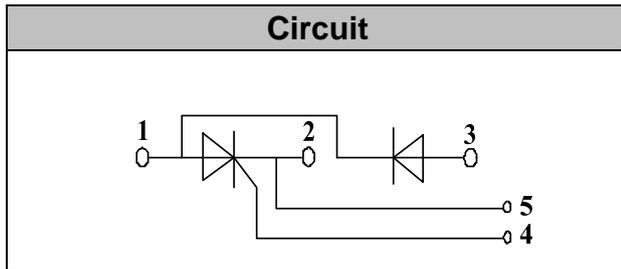


## Thyristor/Diode Modules

**VRRM / VDRM** 800 to 1800V  
**IFAV / ITAV** 60Amp

### Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control



### Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBC ceramic isolated metal baseplate
- UL recognized applied for file no. E360040

### Module Type

| TYPE       | VRRM/VDRM | VRSM  |
|------------|-----------|-------|
| MT60CB08T1 | 800V      | 900V  |
| MT60CB12T1 | 1200V     | 1300V |
| MT60CB16T1 | 1600V     | 1700V |
| MT60CB18T1 | 1800V     | 1900V |

### ◆Diode

#### Maximum Ratings

| Symbol           | Item                               | Conditions           | Values      | Units            |
|------------------|------------------------------------|----------------------|-------------|------------------|
| ID               | Output Current(D.C.)               | Tc=85°C              | 60          | A                |
| IFSM             | Surge forward current              | t=10mS Tvj =45°C     | 1500        | A                |
| i <sup>2</sup> t | Circuit Fusing Consideration       |                      | 11000       | A <sup>2</sup> s |
| Visol            | Isolation Breakdown Voltage(R.M.S) | a.c.50HZ;r.m.s.;1min | 3000        | V                |
| Tvj              | Operating Junction Temperature     |                      | -40 to +125 | °C               |
| Tstg             | Storage Temperature                |                      | -40 to +125 | °C               |
| Mt               | Mounting Torque                    | To terminals(M5)     | 3±15%       | Nm               |
| Ms               |                                    | To heatsink(M6)      | 5±15%       | Nm               |
| Weight           | Module (Approximately)             |                      | 100         | g                |

#### Thermal Characteristics

| Symbol   | Item                    | Conditions       | Values | Units |
|----------|-------------------------|------------------|--------|-------|
| Rth(j-c) | Thermal Impedance, max. | Junction to Case | 0.29   | °C/W  |
| Rth(c-s) | Thermal Impedance, max. | Case to Heatsink | 0.10   | °C/W  |

#### Electrical Characteristics

| Symbol | Item                                  | Conditions          | Values |      |      | Units |
|--------|---------------------------------------|---------------------|--------|------|------|-------|
|        |                                       |                     | Min.   | Typ. | Max. |       |
| VFM    | Forward Voltage Drop, max.            | T=25°C IF =200A     |        |      | 1.65 | V     |
| IRRM   | Repetitive Peak Reverse Current, max. | Tvj =25°C VRD=VRRM  | ≤0.5   |      |      | mA    |
|        |                                       | Tvj =125°C VRD=VRRM | ≤6     |      |      | mA    |



## ◆Thyristor

### Maximum Ratings

| Symbol     | Item   | Conditions  | Values        | Units              |
|------------|--|---|---------------|--------------------|
| $I_{TAV}$  | Average On-State Current                         | Sine 180°; $T_c=85^{\circ}\text{C}$   | 60            | A                  |
| $I_{TSM}$  | Surge On-State Current                           | $T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ , sine<br>$T_{VJ}=125^{\circ}\text{C}$ $t=10\text{ms}$ , sine | 1500<br>1250  | A                  |
| $i^2t$     | Circuit Fusing Consideration                     | $T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ , sine<br>$T_{VJ}=125^{\circ}\text{C}$ $t=10\text{ms}$ , sine | 11000<br>8000 | A <sup>2</sup> s   |
| $V_{isol}$ | Isolation Breakdown Voltage(R.M.S)               | a.c.50HZ;r.m.s.;1min  | 3000          | V                  |
| $T_{vj}$   | Operating Junction Temperature                   |   | -40 to +125   | $^{\circ}\text{C}$ |
| $T_{stg}$  | Storage Temperature                              |   | -40 to +125   | $^{\circ}\text{C}$ |
| $M_t$      | Mounting Torque                                  | To terminals(M5)  | $3 \pm 15\%$  | Nm                 |
| $M_s$      |  | To heatsink(M6)   | $5 \pm 15\%$  | Nm                 |
| $di/dt$    | Critical Rate of Rise of On-State Current        | $T_{VJ}=T_{VJM}$ , $2/3V_{DRM}$ , $I_G=500\text{mA}$<br>$T_r < 0.5\mu\text{s}$ , $t_p > 6\mu\text{s}$     | 150           | A/ $\mu\text{s}$   |
| $dv/dt$    | Critical Rate of Rise of Off-State Voltage, min. | $T_J=T_{VJM}$ , $2/3V_{DRM}$ linear voltage rise  | 1000          | V/ $\mu\text{s}$   |
| $a$        | Maximum allowable acceleration                   |   | 50            | $\text{m/s}^2$     |

### Thermal Characteristics

| Symbol        | Item                    | Conditions       | Values | Units                |
|---------------|-------------------------|------------------|--------|----------------------|
| $R_{th(j-c)}$ | Thermal Impedance, max. | Junction to Case | 0.57   | $^{\circ}\text{C/W}$ |
| $R_{th(c-s)}$ | Thermal Impedance, max. | Case to Heatsink | 0.20   | $^{\circ}\text{C/W}$ |

### Electrical Characteristics

| Symbol            | Item  | Conditions   | Values |      |      | Units            |
|-------------------|---|--|--------|------|------|------------------|
|                   |   |  | Min.   | Typ. | Max. |                  |
| $V_{TM}$          | Peak On-State Voltage, max.   | $T=25^{\circ}\text{C}$ $I_T=200\text{A}$   |        |      | 1.65 | V                |
| $I_{RRM}/I_{DRM}$ | Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max. | $T_{VJ}=T_{VJM}$ , $V_R=V_{RRM}$ , $V_D=V_{DRM}$                                 |        |      | 15   | mA               |
| $V_{TO}$          | On state threshold voltage  | For power-loss calculations only<br>( $T_{VJ}=125^{\circ}\text{C}$ )             |        |      | 0.9  | V                |
| $r_T$             | Value of on-state slope resistance. max   | $T_{VJ}=T_{VJM}$   |        |      | 3.5  | $\text{m}\Omega$ |
| $V_{GT}$          | Gate Trigger Voltage, max.  | $T_{VJ}=25^{\circ}\text{C}$ , $V_D=6\text{V}$                                    |        |      | 3.0  | V                |
| $I_{GT}$          | Gate Trigger Current, max.  | $T_{VJ}=25^{\circ}\text{C}$ , $V_D=6\text{V}$                                    |        |      | 150  | mA               |
| $V_{GD}$          | Non-triggering gate voltage, max.   | $T_{VJ}=125^{\circ}\text{C}$ , $V_D=2/3V_{DRM}$                                  |        |      | 0.25 | V                |
| $I_{GD}$          | Non-triggering gate current, max.   | $T_{VJ}=125^{\circ}\text{C}$ , $V_D=2/3V_{DRM}$                                  |        |      | 6    | mA               |
| $I_L$             | Latching current, max.  | $T_{VJ}=25^{\circ}\text{C}$ , $R_G=33\Omega$                                     | 300    |      | 600  | mA               |
| $I_H$             | Holding current, max.   | $T_{VJ}=25^{\circ}\text{C}$ , $V_D=6\text{V}$                                    | 150    |      | 250  | mA               |
| $t_{gd}$          | Gate controlled delay time  | $T_{VJ}=25^{\circ}\text{C}$ ,<br>$I_G=1\text{A}$ , $di/dt=1\text{A}/\mu\text{s}$ |        | 1    |      | $\mu\text{s}$    |
| $t_q$             | Circuit commutated turn-off time  | $T_{VJ}=T_{VJM}$   |        | 80   |      | $\mu\text{s}$    |



## Performance Curves

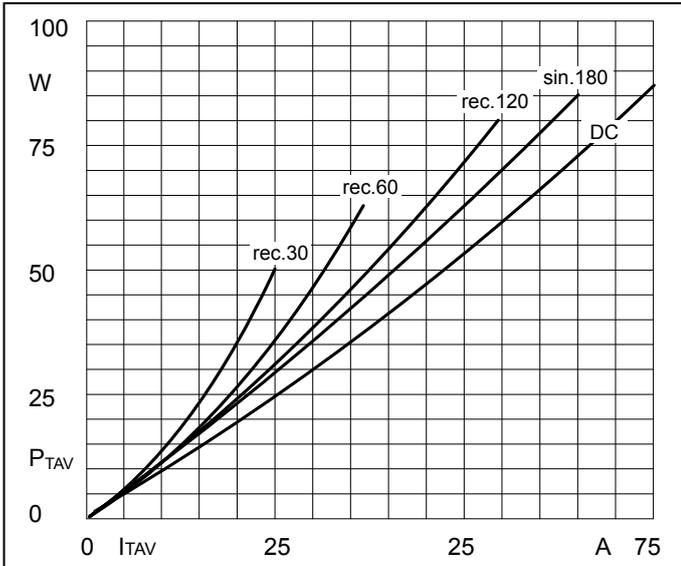


Fig1. Power dissipation

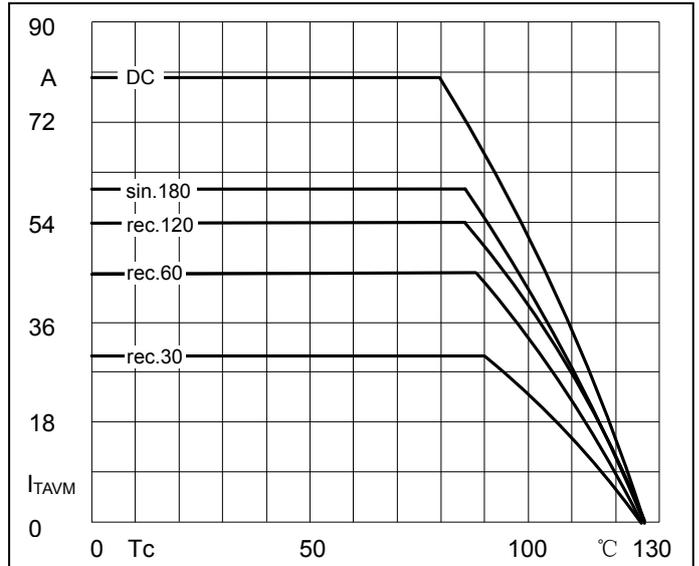


Fig2. Forward Current Derating Curve

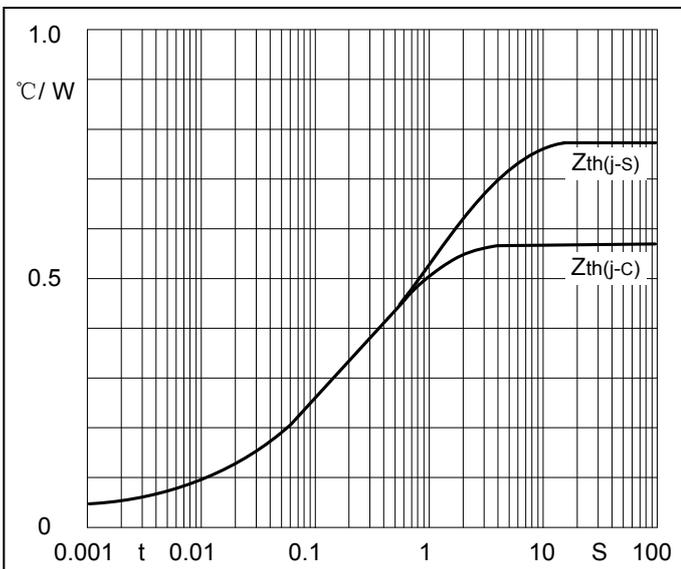


Fig3. Transient thermal impedance

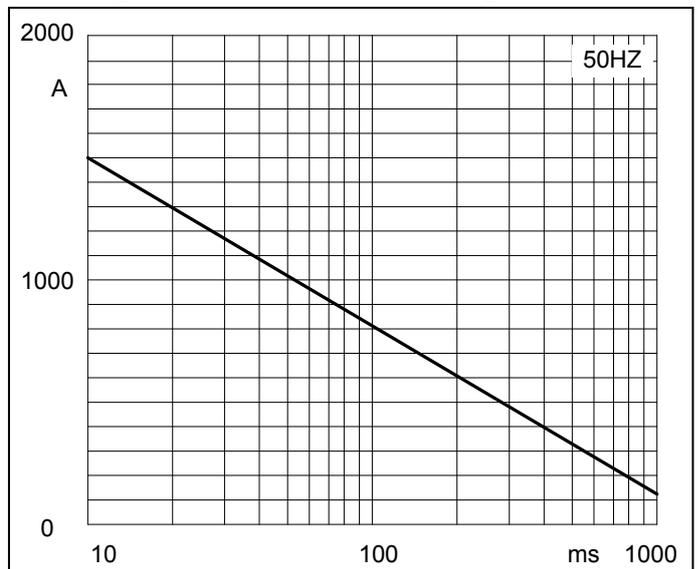


Fig4. Max Non-Repetitive Forward Surge Current

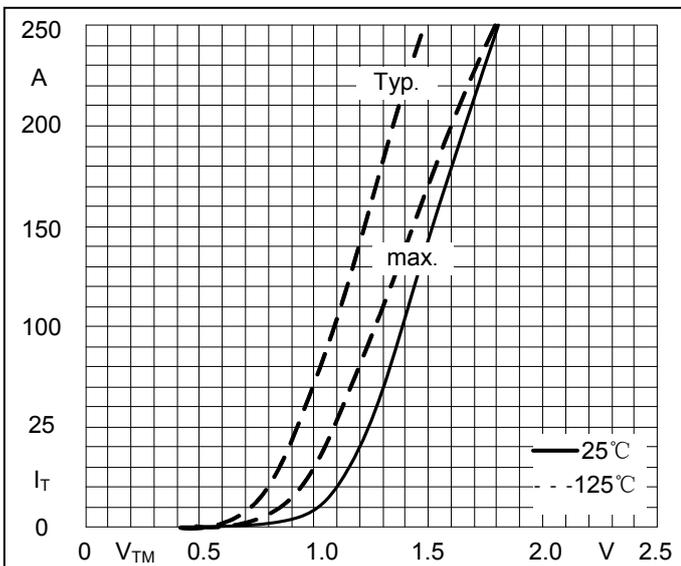


Fig5. Forward Characteristics

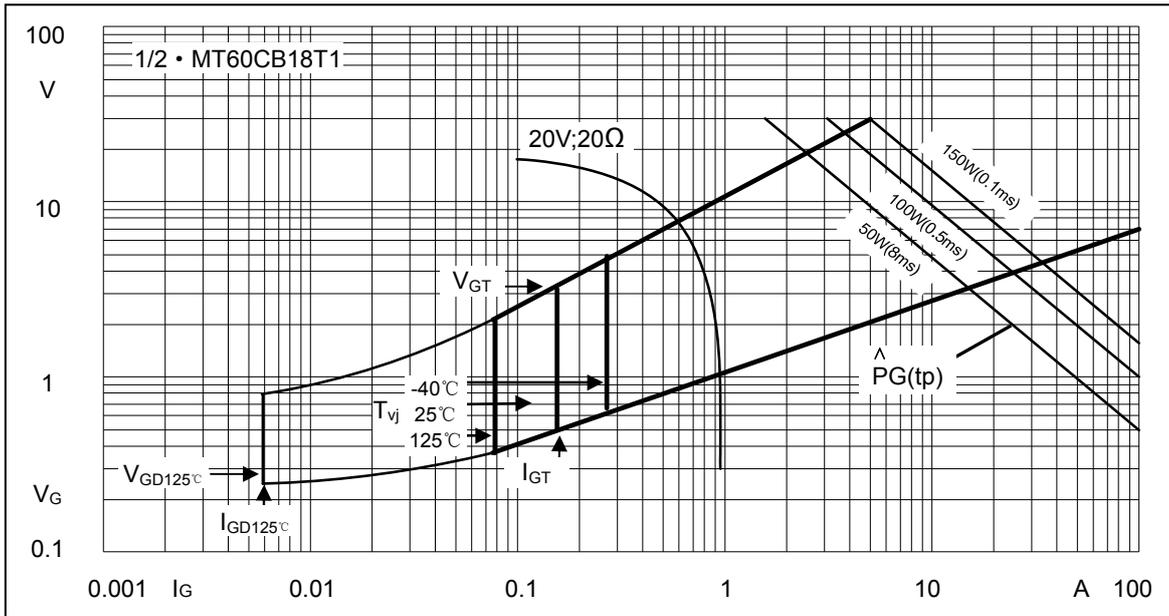
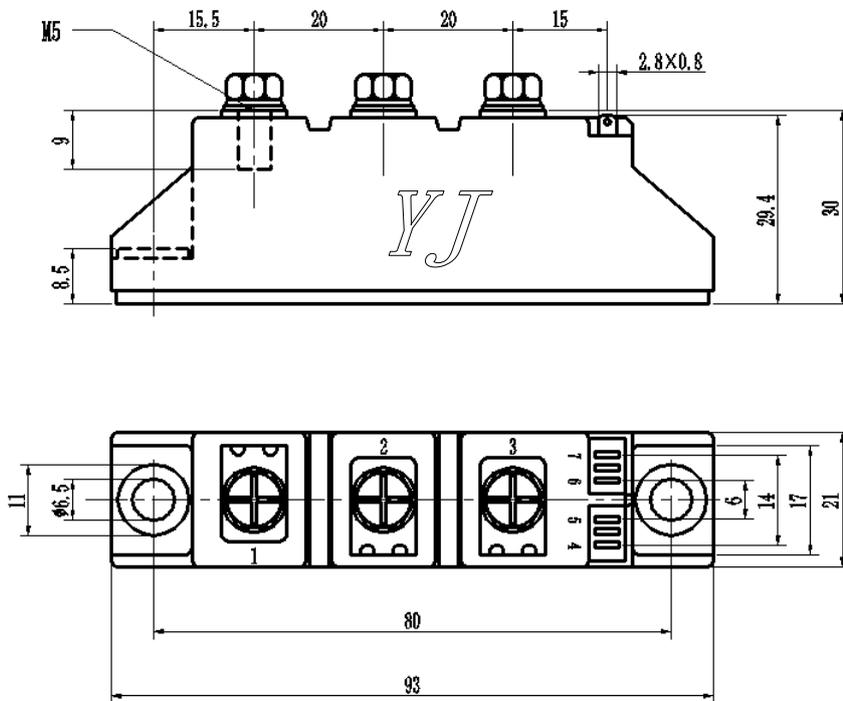


Fig6. Gate trigger Characteristics

## Package Outline Information

### CASE: T1



Dimensions in mm